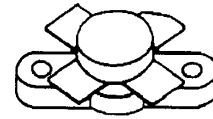


MS1076
**RF & MICROWAVE TRANSISTORS
HF SSB APPLICATIONS**
Features

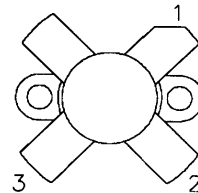
- 30 MHz
- 28 VOLTS
- GOLD METALLIZATION
- $P_{OUT} = 220$ W PEP
- $G_P = 12$ dB GAIN MINIMUM
- COMMON EMITTER CONFIGURATION



.500 4LFL (M174)
epoxy sealed

DESCRIPTION:

The MS1076 is a 28 volt epitaxial NPN silicon planar transistor designed primarily for SSB and VHF communications. This device utilizes an emitter ballasted die geometry for maximum ruggedness and reliability.

PIN CONNECTION


1. Collector 3. Base
2. Emitter 4. Emitter

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector - Base Voltage	70	V
V_{CEO}	Collector - Emitter Voltage	35	V
V_{EBO}	Emitter - Base Voltage	4.0	V
I_C	Device Current	16	A
P_{DISS}	Power Dissipation	250	W
T_J	Junction Temperature	+200	°C
T_{STG}	Storage Temperature	- 65 to +150	°C

Thermal Data

$R_{TH(J-C)}$	Junction - Case Thermal Resistance	0.7	°C/W
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Rev A: October 2009

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV _{CES}	I _C = 100 mA	70	---	---	V
BV _{CEO}	I _C = 200 mA	35	---	---	V
BV _{EBO}	I _E = 20 mA	4.0	---	---	V
I _{CEO}	V _{CE} = 30 V	---	---	5	mA
I _{CES}	V _{CE} = 35 V	---	---	5	mA
H _F E	V _{CE} = 5 V, I _C = 7 A	15	---	60	---

DYNAMIC

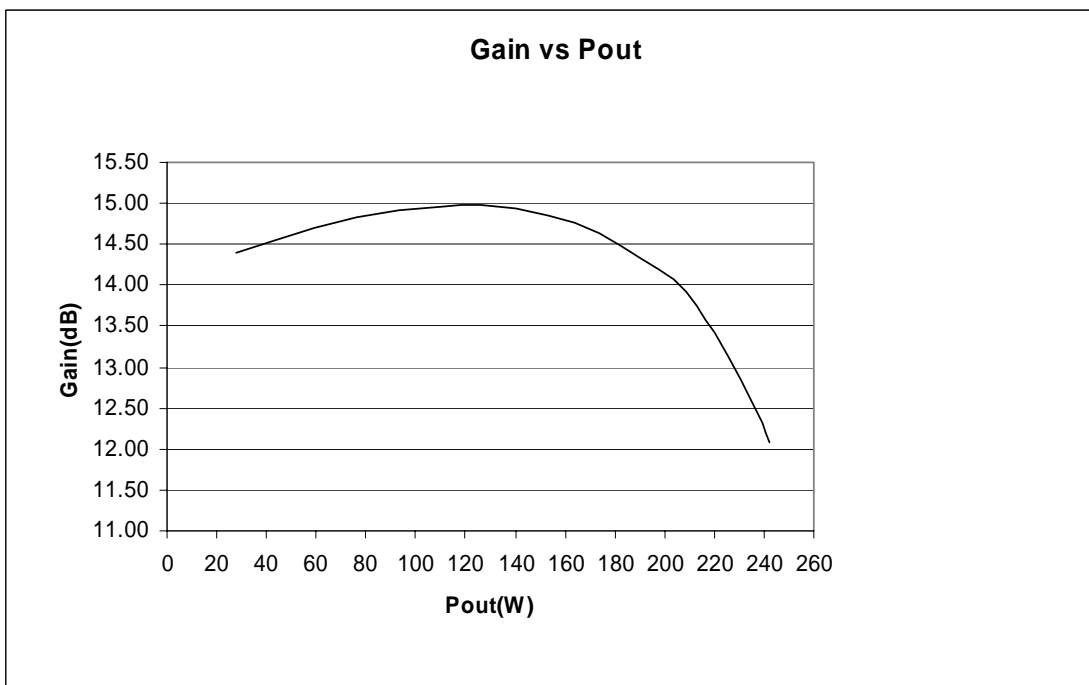
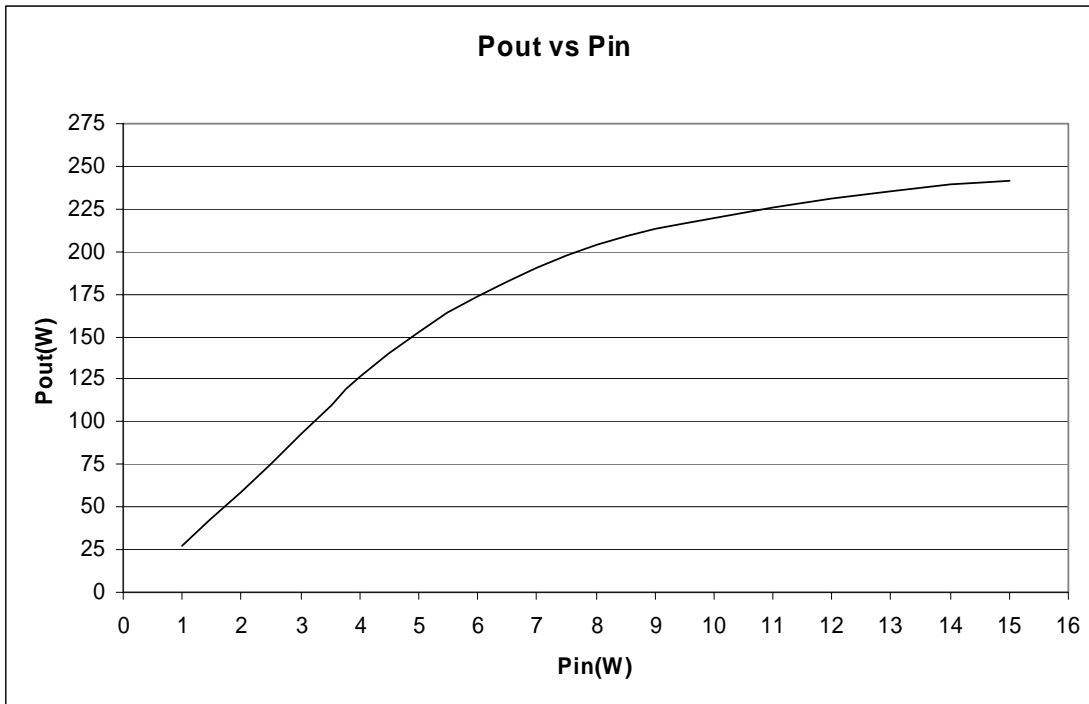
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 30 MHz	V _{CE} = 28 V	I _{CQ} = 750 mA	220	---	---	WPEP
G _P	f = 30 MHz	V _{CE} = 28 V	I _{CQ} = 750 mA	12	---	---	dB
η _C	f = 30 MHz	V _{CE} = 28 V	I _{CQ} = 750 mA	40	---	---	%
IMD	f = 30 MHz	V _{CE} = 28 V	I _{CQ} = 750 mA	---	---	-30	dBc
C _{OB}	f = 1 MHz	V _{CB} = 28 V		---	450	---	pf
Conditions	f1 = 30.000 MHz	f2 = 30.001 MHz					

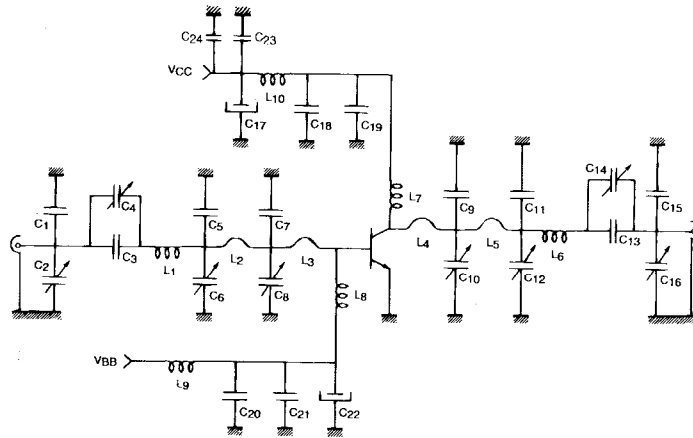
HFE BINNING (marked on lid with appropriate letter):

A = 15-19	D = 27-32	G = 45-50
B = 19-22.5	E = 32-38	H = 50-55
C = 22.5-27	F = 38-45	I = 55-60

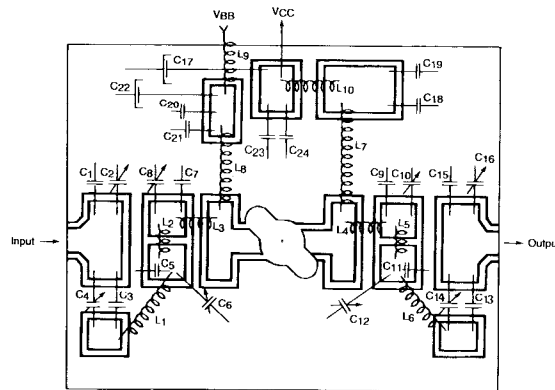
IMPEDANCE DATA

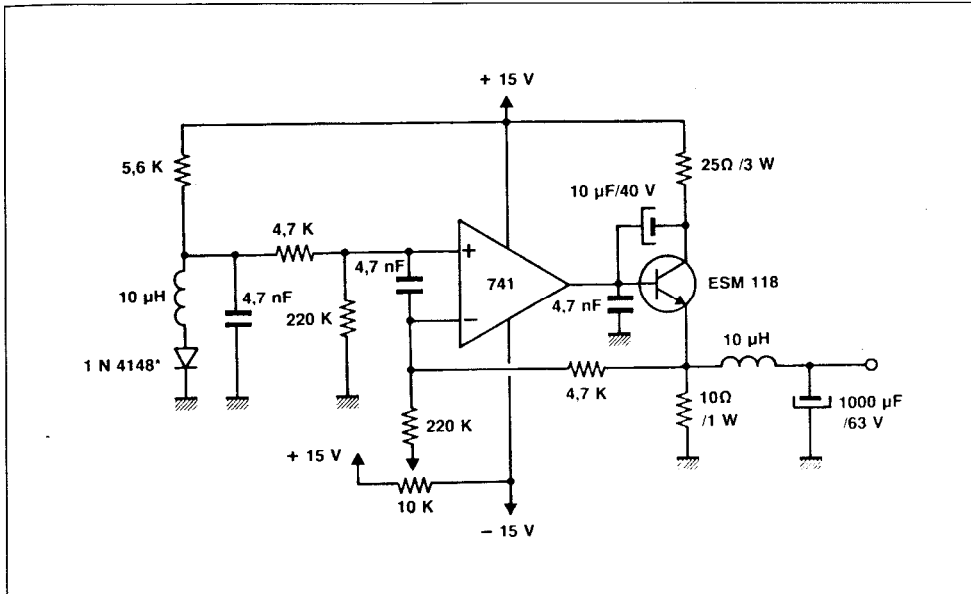
FREQ	Z _{IN}	Z _{CL}
30 MHz	1.2 + j0.41	1.25 + j1.92

TYPICAL PERFORMANCE

TEST CIRCUIT
TEST CIRCUIT


C1 : 180pF	L1 : 3 Turns, Diameter 10mm, 1.3mm Wire, Length 10mm
C2, C4, C6, C8, C10, C12	L2, L5 : Hair Pin Copper foil 40 x 5mm, 0.2mm Thick
C14, C16 : Arco 428	L3, L4 : Hair Pin Copper Foil 10 x 5mm, 0.2mm Thick
C3 : 820pF	L6 : 5 Turns, Diameter 10mm, 1.3mm Wire, Length 15mm
C5, C13 : 680pF	L7 : 3 Turns, Diameter 10mm, 1.3mm Wire, Length 25mm
C7, C11 : 1.2nF	L8 : Choke
C9 : 1.5nF	L9 : Choke
C17, C22 : 470µF, 40V	L10 : Choke
C18 : 10nF	
C19, C21	
C23 : 1nF	
C20, C24 : 100nF, 63V	



BIAS CIRCUIT

PACKAGE MECHANICAL DATA

